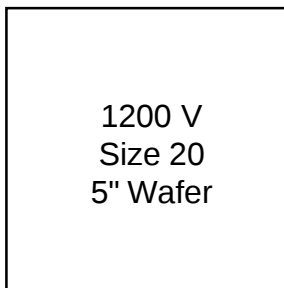


Hexfred Die in Wafer Form



Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	3.0V Max.	$T_J = 25^{\circ}C$, $I_F = 6.0A$
BV_R	Reverse Breakdown Voltage	1200V Min.	$T_J = 25^{\circ}C$, $I_R = 200\mu A$
I_{RM}	Reverse Leakage Current	5 μA Max.	$T_J = 25^{\circ}C$, $V_R = 1200V$

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr-Ni-Ag (1kA-4kA-6kA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.130" x 0.107"
Wafer Diameter	125mm, with std. < 100 > flat
Wafer Thickness	.015" $\pm$.003"
Relevant Die Mechanical Dwg. Number	01-5165
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : HFA06TB120

Die Outline

